

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,041,599 B1
APPLICATION NO. : 09/469709
DATED : May 9, 2006
INVENTOR(S) : Shijan Li et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1, Line 47: Change "(w)" to --(W)--

Column 3, Line 9: Change the semicolon to a comma

Column 3, Line 29: Change "particular" to --particularly--

Column 5, Line 47: Before "interlayer", change "a" to --an--

Column 6, Line 37: Change "iminodiaetic" to --iminodiacetic--

Column 7, Line 13: After "manner", insert --with abrasive, to remove to Ta or TaN barrier layer, under conditions such that there is no or reversed selectivity among the silicon oxide interlayer dielectric, barrier layer and Cu.--

Column 9, Line 50: Change "none" to --one--

Column 10, Line 21: Delete the comma after "instructions"

Column 10, Line 21: After "initially", delete "be"

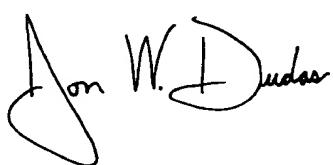
Column 11, Claim 16, Line 58: Before "a computer-readable", delete "comprise"

Column 12, Claim 18, Line 9: Change "iminodiaetic" to --iminodiacetic--

Column 12, Claim 23, Line 50: Change "of" to --is--

Signed and Sealed this

Twelfth Day of September, 2006



JON W. DUDAS
Director of the United States Patent and Trademark Office